

XPS – as a versatile tool in the research of the Department of Inorganic and Physical chemistry, UGent

Els Bruneel, V Narayanan, G. Penneman, I. Muyllaert B. De Gusseme, A. Swhwarz, L. Van Langenhove P. VanderVoort, I. Van Driessche

Annual XPS –users meeting 16–10–2009



Content

- Thin film superconducting materials by sol gel chemistry
- Fibrous transistors, in cooperation with dep. of Textiles, Ugent
- Biogenic nanoparticles, in cooperation with labMET
- Supported metal oxide catalyst for liquid oxidation reactions



Principle



Deposition on substrates by dipcoating, printing

Gelation, T≤60°C



Heat treatment under controlled atmosphere







Sol



Gel

oxide thin film (5-100 nm)



Deposition

- dip-/spin-coating from aqueous solutions
- ink-jet printing from water-based inks



liquid precursorlayer



Analysis of solutions, gels and thin films:

- optical analysis : UV/Vis/IR/Raman spectroscopy
- rheology : viscosity, surface tension, contact angle, particle size, ...
- thermal analysis : TGA/DTA/DSC/TMA
- microscopy : AFM, optical, SEM/EDX, (HR)TEM with EELS, STEM, EDX
- structural analysis : XRD, pole figures, BET
- electromagnetic : resistivity measurements
- complexometry : potentiometric titrations
- XPS

Materials

- ceramic high T_c superconductor architectures on NiW tapes : YBCO, CeO₂, La₂Zr₂O₇
- TiO₂ for self-cleaning surfaces : on ceramic tiles and steel
- YSZ for thermal barrier coatings and solid oxide fuel cells
- mesoporous organosilica layers for low-k dielectrics (through ...)
- Diesel soot catalyst



High T_c superconductor architecture :





Applications :

- -resistance ~0 at -180 °C
- second generation HTS wires
- fault current limiter
- magnets
- coils for renewable energy
- induction heaters ...

High T_c superconductor HTS architecture: XPS, TEM, FIB

(HR)-TEM analysis of interface, surface, crystalinity/texture

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Cs-corrected TEM equiped with EELS, STEM, EDX ...

Sputter XPS analysis depth profiling

- Ni diffusion through buffer layers for ≠ processing
- determination of layer thickness
- compositional analysis
- degree of oxidation

UNIVERSITEIT GENT Study of oxidation state of Cerium and Ni-diffusion, a single layer pHd Greet Penneman (2007) Escalab 250 (VG Scientific)

 Ce^{+4} ion : (Xe) = 5p⁶ 4f⁰

Ce⁺³ ion: (Xe) $4f^{1} = 5p^{6} 4f^{1}$

Ce-O is not 100 % ionic

Ce: 5p ⁶ 4f ⁰	O: 1s ² 2s ² 2p ⁶		lonic:	Ce: 5p ⁶ 4f ¹	O: 1s ² 2s ² 2p ⁶
Ce: 5p ⁶ 4f ¹)		less ionic:	Ce: 5p ⁶ 4f ²	
Ce: 5p ⁶ 4f ²					
i's notation:	V ₀	v	\mathbf{v}'	v″	v‴
Origin Shift (eV)	Ce^{3+}	Ce ⁴⁺	Ce ³⁺	Ce^{4+}	Ce ⁴⁺
FWHM	4.11	5.77	3.76	2.69	3.96
	u ₀	u	u′	u″	u‴
Origin	Ce ³⁺	Ce ⁴⁺	Ce ³⁺	Ce^{4+}	Ce ⁴⁺
Shift (eV) FWHM	-17.8 3.91	-15.65 5.86	-13.65 4.00	-9.25 4.64	0 1.39
	Ce: 5p ⁶ 4f ⁰ Ce: 5p ⁶ 4f ¹ Ce: 5p ⁶ 4f ² I's notation: Origin Shift (eV) FWHM Origin Shift (eV) FWHM	Ce: $5p^{6} 4f^{0}$ O: $1s^{2} 2s^{2} 2p^{6}$ Ce: $5p^{6} 4f^{1}$ Ce: $5p^{6} 4f^{2}$ Ce: $5p^{6} 4f^{2}$ Ce: $5p^{6} 4f^{2}$ Origin Ce ³⁺ Shift (eV) -36.1 FWHM 4.11 $\frac{u_{0}}{0}$ Origin Ce ³⁺ Shift (eV) -17.8 FWHM 3.91	Ce: $5p^{6} 4f^{0}$ O: $1s^{2} 2s^{2} 2p^{6}$ Ce: $5p^{6} 4f^{1}$ Ce: $5p^{6} 4f^{2}$ Ce: $5p^{6} 4f^{2}$ Ce: $5p^{6} 4f^{2}$ Cei $big in ce^{3+}$ Ce ⁴⁺ Shift (eV) -36.1 -34.1 FWHM 4.11 5.77 u_{0} u Origin Ce ³⁺ Ce ⁴⁺ Shift (eV) -17.8 -15.65 FWHM 3.91 5.86	$\begin{array}{cccccccccccccccccccccccccccccccccccc$	$\begin{array}{cccccccccccccccccccccccccccccccccccc$

UNIVERSITEIT GENT Study of oxidation state of Cerium and Ni-diffusion, a single layer pHd Greet Penneman (2007) Escalab 250 (VG Scientific)

XPS narrow scan of the Ce 3d region showing the typical spectrum for Ce⁴⁺.

Fitting: contstraints: doublet separation, peak position, FWHM, peak shape

Top: Ce (IV) Core: Ce (III) Due to sputtering?

Continuation : Multiple layers, Vyshnavi Narayanan

The objective is to study the role of buffer layers in transferring the texture of Ni-W substrate to YBCO (XRD) and its effective role in prevention of penetration of Ni into YBCO

CeO-LZO-CeO on Ni-W

CeO-LZO-CeO on Ni-W 100 2000 ← C1s (001)90 Ce3d 1800 La3d5/2 80 1600 Zr3d 70 Atom percentage - Ni2p1/2 1400 ← W4f 60 1200 01s 50 1000 40 800 30 600 20 400 (W)10 200 (111)۵ 100 0 50 150 200 250 300 350 400 450 500 Π 26 27 31 32 33 34 25 28 29 30 35 Sputtering time in seconds XPS etching \leftarrow \rightarrow XRD spectrum CeO₂ $\mathcal{E}eO_2$ LZO

"Multiple buffer layer architecture in HTSC- Deposition and characterization" V. Narayanan, V. Cloet, N. Van de Velde, P. Lommens, K. De Buysser, E. Bruneel, I. Van Driessche and S. Hoste, Eucas 2009, Berlin

UNIVERSITEIT Biogenic metals: XPS analysis of cerium from organic origin

B. De Gusseme, Prof. Verstraete (LabMET)

Goal:

In a biological process cerium-ions are removed from a solution into a solid state. The question was to identify the oxidation number of the cerium in the solid state.

The paste like substance was spread onto a Snsubstrate. It is shown that the presence of cerium in the sample could be confirmed. The oxidation state of the cerium is Ce(III)

Oxidation	BE (eV)		
state			
Ce(IV)	898.4	3d ^{5/2}	
	916.9	3d ^{3/2}	
Ce(IV)	888.9	3d ^{5/2}	
	907.5	3d ^{3/2}	
Ce(IV)	882.3	3d ^{5/2}	
	901.0	3d ^{3/2}	
Ce(III)	880	3d ^{5/2}	
	899	3d ^{3/2}	
Ce(III)	886	3d ^{5/2}	
	904	3d ^{3/2}	

Table 1: Overview

Ce3d^{3/2} and 3d^{5/2}

Illustration: TEM of zerovalent paladium particles precipitated at the cell surface of Shewanella oneidesis

Biogenic metals in advanced water treatment TRENDS IN BIOTECHNOLOGY 27,2, 90–98 FEB 2009 Tom Hennebel, Bart De Gusseme, Nico Boon, Willy Verstraete, UGENT

Textile based transistor UNIVERSITEIT Dep. Textiles A. Swhwarz, prof. Van Langenhove

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Steps towards a textile based transistor – Development of the gate and insulating layer, A. Schwarz, J. Cardoen, E. Bruneel, J. Hakuzimana, Philippe Westbroek, S.Hoste, Lieva Van Langenhove, submitted

Ultra-stable and zero leaching supported metal oxide catalyst for liquid oxidation reactions

Study of Vanadiumoxide on mesoporous fenol resins Ilke Muylaert, prof. Van Der Voort

Vanadium grafting

Muylaert I, et al., Phys. Chem. Chem. Phys., (2009),

(b)

(c)

(d)

0

V 2p^{3/2}

Thanks